

Wide dynamic logarithmic InGaAs sensor suitable for eye-safe active imaging

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- ❖ Active Imaging Scenarios
- ❖ Basic requirements on Active Imaging
- ❖ NIT's logarithmic ROIC for InGaAs sensor
- ❖ Analysis of ROIC's behavior under short gating
- ❖ Conclusion: NIT Solution for Short Gated Active Imaging

□ Continuous Illumination for

- ✓ (covered) surveillance at night
- ✓ wavelength based discrimination capability



□ Pulsed Illumination for

- ✓ (covered) surveillance at day/night
- ✓ retrodiffusion suppression by distance indexed gating
- ✓ low interception probability
- ✓ target designation/recognition



□ Under Continuous Illumination

- ✓ High dynamic range against NEAR-FAR effect
- ✓ Low noise for lower illumination power
- ✓ Low dark current for long exposure time



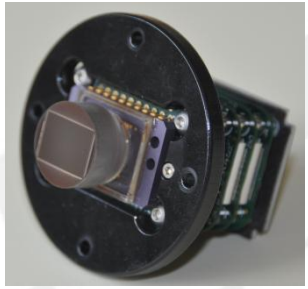
□ Under Pulsed Illumination

- ✓ Short exposure time with good shutter efficiency
- ✓ Low triggering delay
- ✓ Low Jitter
- ✓ High dynamic range with no blooming
- ✓ Ambient background suppression



Active Imaging needs WDR 1

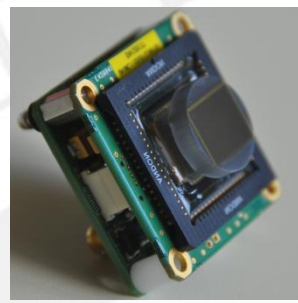
12 Tube Gated Active Imaging



GE1380H
(Sony CCD)

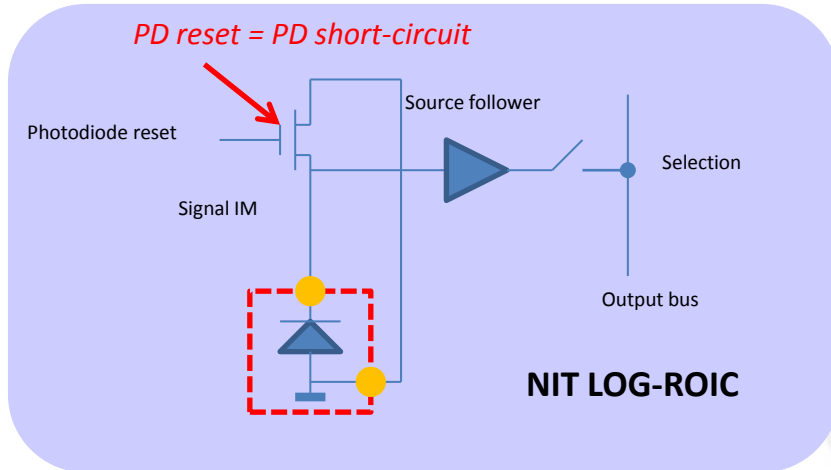


NIT
IMAGIC



Active Imaging needs WDR 2

Continuous active imaging with NIT Widy InGaAs Sensor

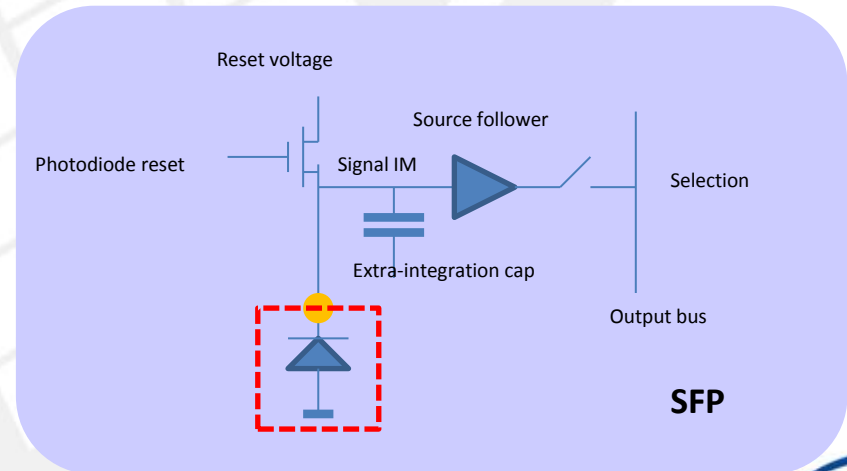
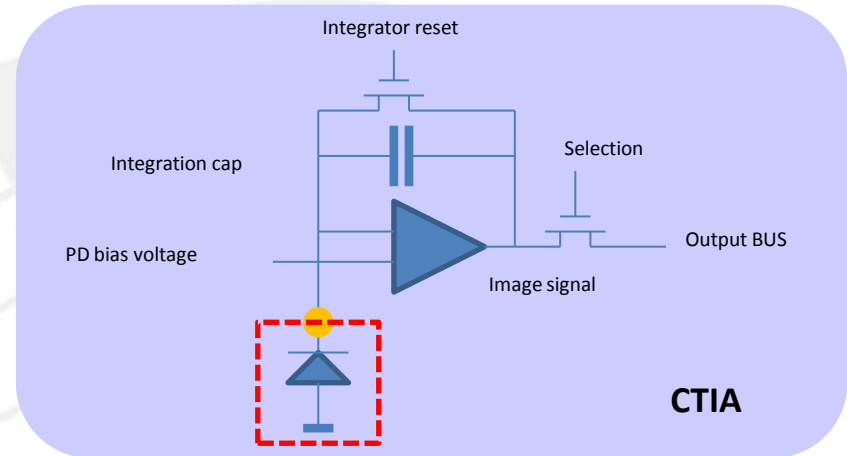
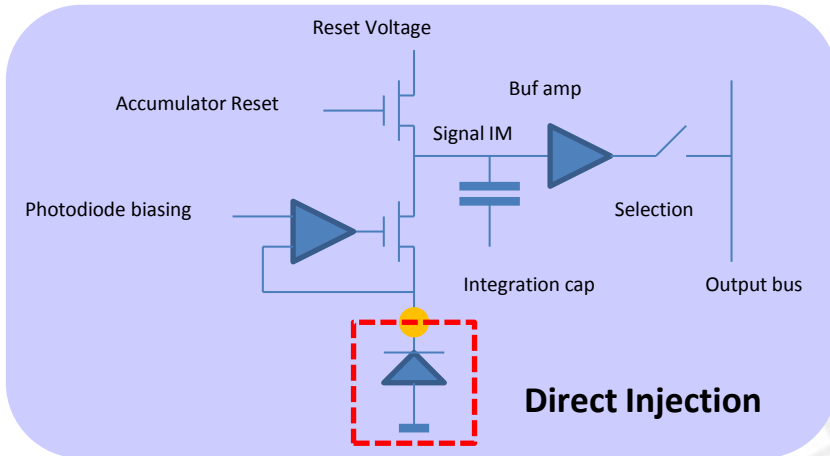


- Photodiode generates active voltage signal
- Very precise/repeatable logarithmic response
- High uniformity due to forward biasing
- Simple design for > 120dB instant DR

**Adequate for
continuous illumination active imaging**

- **Proprietary InGaAs photodiode array**
- Active dark current reduction
- Active Cross-Talk suppression
- 3 international patents filed





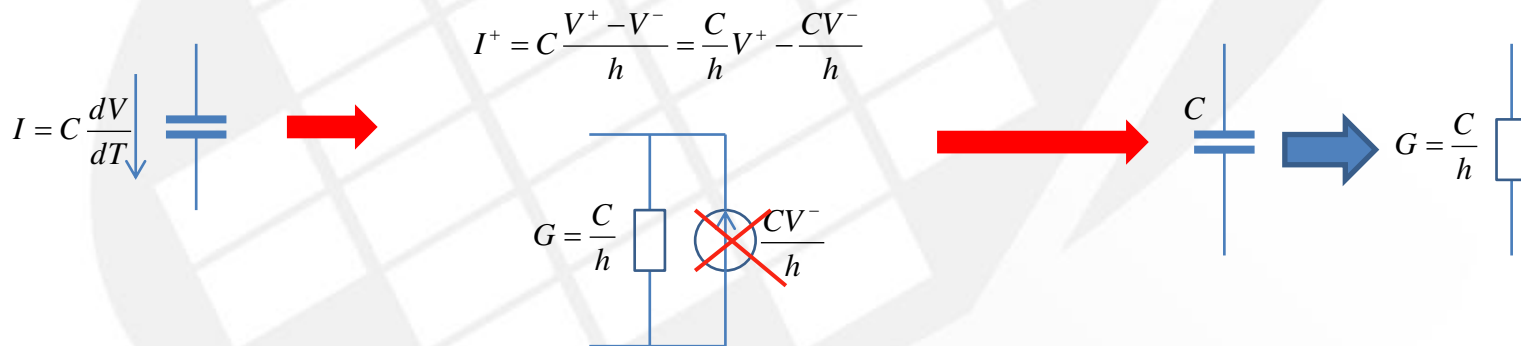
- Fundamentally voltage based designs
- KTC & 1/f noise can be compensated by CDS (ITR)
- 1/f noise can be a problem with long exposure
- What is the impulse response ??
- How to do simple analysis ??

For efficient & powerful design, we need

- ✓ More general design guidance analysis
- ✓ Simple modelling giving optimization possibility

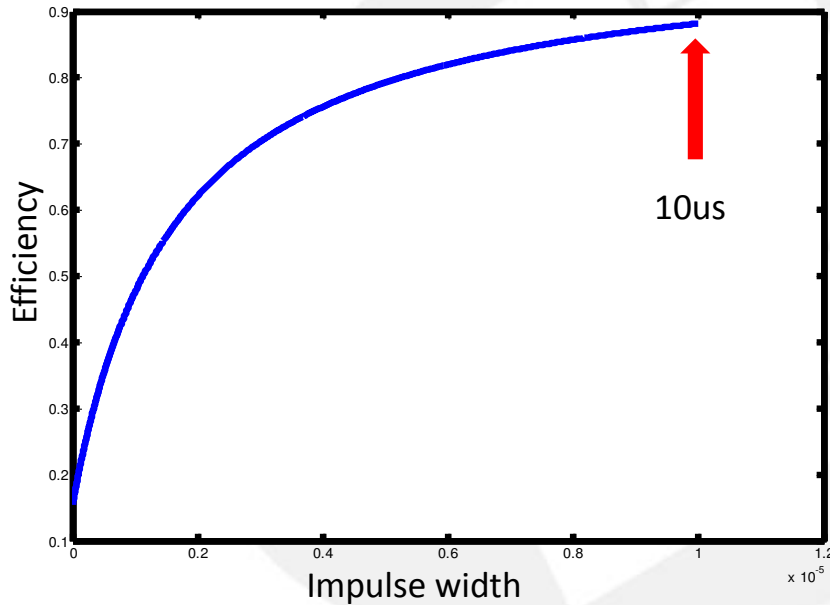
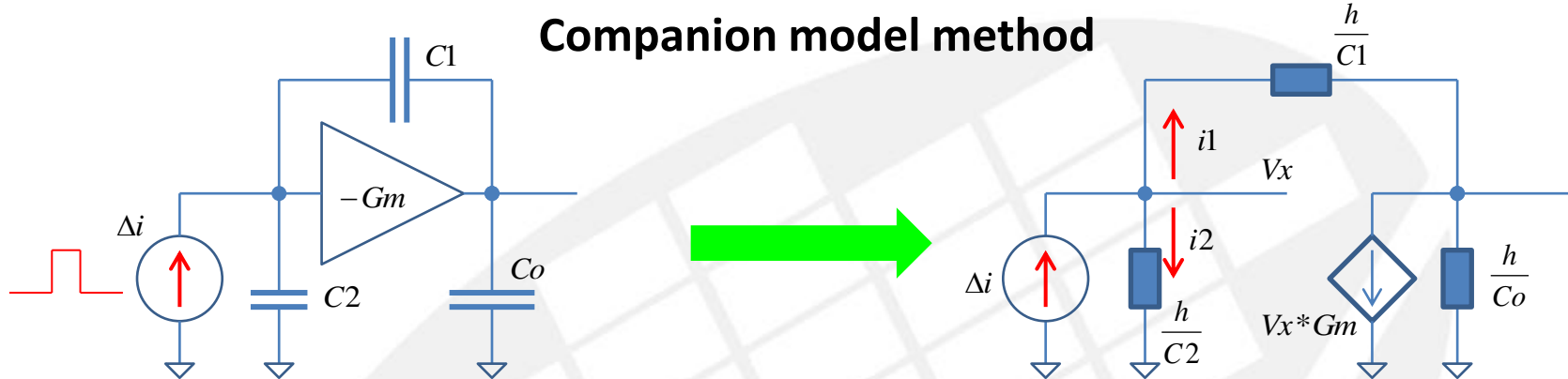
Most of pixel design is based on Gm-C structures

- ✓ impulse width is small (in general)
- ✓ circuit evolution is similar to one time step in SPICE simulation



Injection Efficiency of CTIA under gating

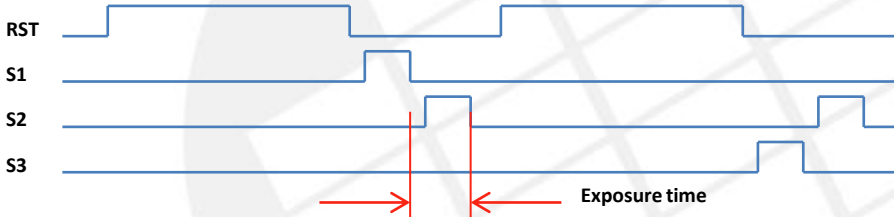
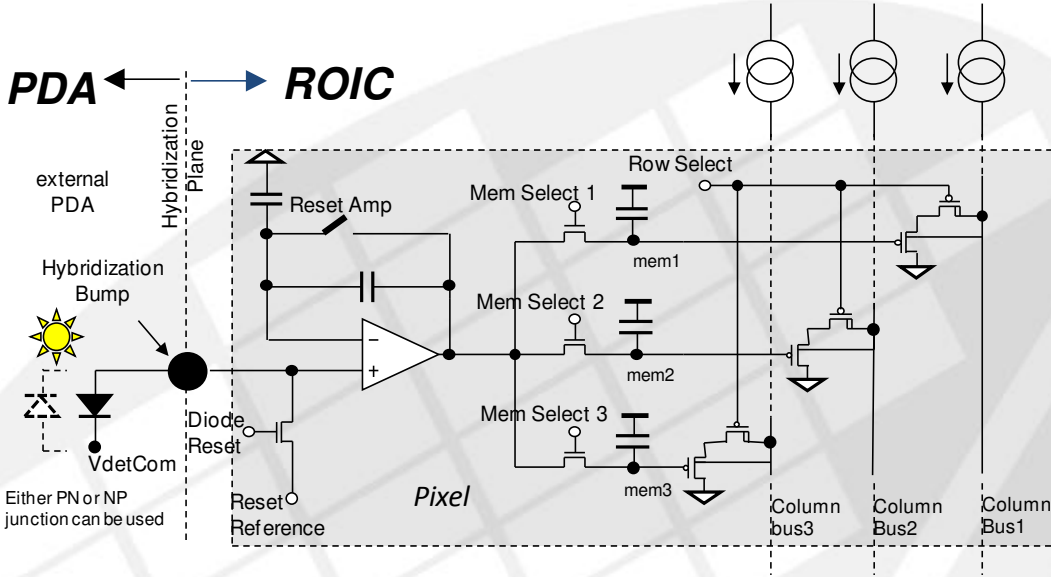
Companion model method



$$\eta = \frac{i_1}{i_1 + i_2} = \frac{C1 * Co + C1 * Gm * h}{(C1 + Co) * C2 + C1 * Co + C1 * Gm * h}$$

← $C1 = 10\text{fF}, C2 = 50\text{fF}, Co = 100\text{fF}$
 $Gm = 0.4\mu\text{S} (Id = 0.1\mu\text{A}, V_{eff} = 0.5)$

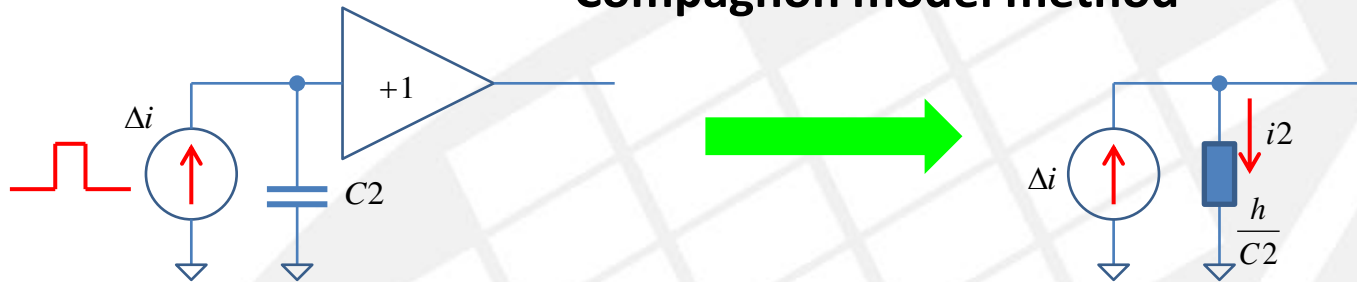
- ✓ Loss of integration efficiency with pulse width in CTIA
- ✓ Loss of integration efficiency with conversion gain
- ✓ High Gm device is needed



IWR with in-pixel CDS

- ✓ 3 in-pixel memory for true CDS
- ✓ Flexible control for multi-mode operation
- ✓ Short exposure time (<200ns possible)
- ✓ Low noise (<150 electrons)
- ✓ Low power consumption

Compagnon model method

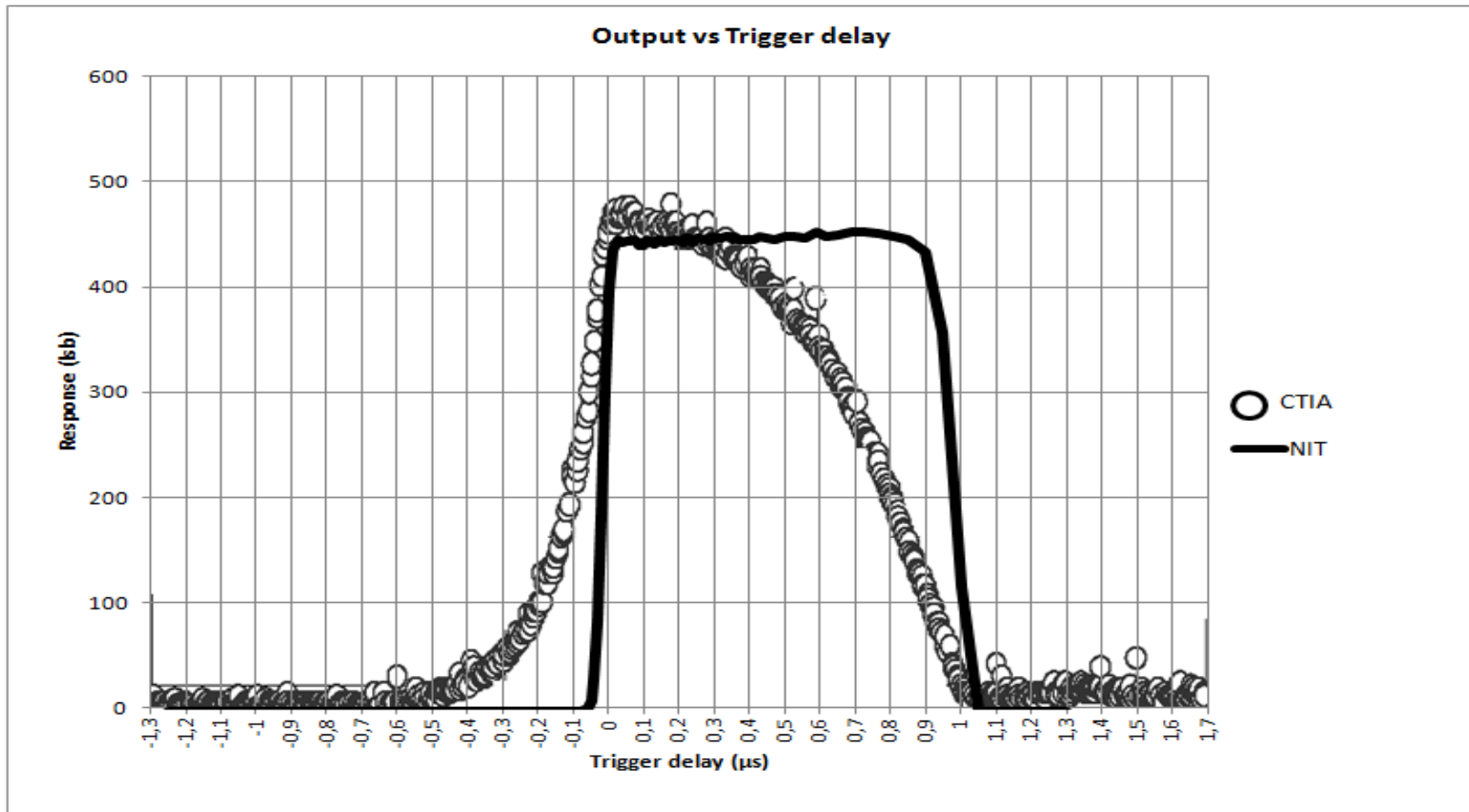


- ✓ **100% integration efficiency**
- ✓ **Low conversion gain**
- ✓ **SF noise is critical !**
- ✓ **Compatible with NIT Logarithmic Pixel design**

NIT Solution for Gated AI

- Compact and low power consumption SWIR camera
- Very short exposure time down to 200ns
- Very low latency : 200ns
- Very low jitter <10ns
- Adjustable trigger delay for spatial scanning with steps <30ns
- Very efficient global shutter gating





- ✓ High and Constant injection efficiency
- ✓ Highly efficient shutter at high speed

Thank you for your attention

Please visit our booth # 302 for live demo

Or for further questions contact:

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